

0.7-Ω DUAL SPDT ANALOG SWITCH WITH NEGATIVE RAIL CAPABILITY AND 1.8-V COMPATIBLE INPUT LOGIC

Check for Samples: [TS5A22366](#)

FEATURES

- **Negative Signaling Capability:** Maximum Swing From -2.75 V to 2.75 V ($V_+ = 2.75\text{ V}$)
- **Low ON-State Resistance ($0.7\text{ }\Omega$ Typ)**
- **Excellent ON-State Resistance Matching**
- **1.8-V Compatible Control Input Threshold Independent of V_+**
- **Control Inputs Are 5.5-V Tolerant**
- **2.25-V to 5.5-V Power Supply (V_+)**
- **Low Charge Injection**
- **Specified Break-Before-Make Switching**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**

- **ESD Performance Tested Per JESD 22**
 - 2500-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)
 - 200-V Machine Model (A115-A)

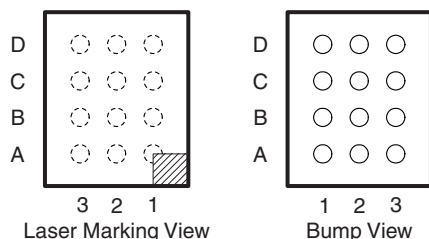
APPLICATIONS

- Cell Phones
- PDAs
- Portable Instrumentation
- Audio Routing
- Portable Media Players

YFC PACKAGE TERMINAL ASSIGNMENTS

D	NC1	V_+	NC2
C	COM1	GND	COM2
B	NO1	GND	NO2
A	IN1	N.C. ⁽¹⁾	IN2
	1	2	3

YFC PACKAGE



(1) N.C. –No internal connection

DESCRIPTION

The TS5A22366 is a dual single-pole double-throw (SPDT) analog switch that is designed to operate from 2.25 V to 5.5 V. The device features negative signal capability that allows signals below ground to pass through the switch without distortion.

The break-before-make feature prevents signal distortion during the transferring of a signal from one path to another. Low ON-state resistance, excellent channel-to-channel ON-state resistance matching, and minimal total harmonic distortion (THD) performance are ideal for audio applications.

The TS5A22366 is available is a ultra small 1.6 mm × 1.2 mm wafer-chip-scale package (WCSP) (0.4 mm pitch).

ORDERING INFORMATION

For package and ordering information, see the Package Option Addendum at the end of this document.



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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Table 1. SUMMARY OF CHARACTERISTICS $V_+ = 3.3\text{ V}$, $T_A = 25^\circ\text{C}$

Configuration	2:1 Multiplexer/Demultiplexer (2 × SPDT)
Number of channels	2
ON-state resistance (r_{on})	0.8 Ω
ON-state resistance match (Δr_{on})	0.08 Ω
ON-state resistance flatness ($r_{ON(flat)}$)	0.3 Ω
Turn-on/turn-off time (t_{ON}/t_{OFF})	199 ns/182 ns
Break-before-make time (t_{BBM})	7.1 ns
Charge injection (Q_C)	120 pC
Bandwidth (BW)	32 MHz
OFF isolation (O_{ISO})	–70 dB at 100 kHz
Crosstalk (X_{TALK})	–70 dB at 100 kHz
Total harmonic distortion (THD)	0.01%
Package option	12-pin WCSP (YFC)

Table 2. FUNCTION TABLE

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
H	OFF	ON

APPLICATION BLOCK DIAGRAM

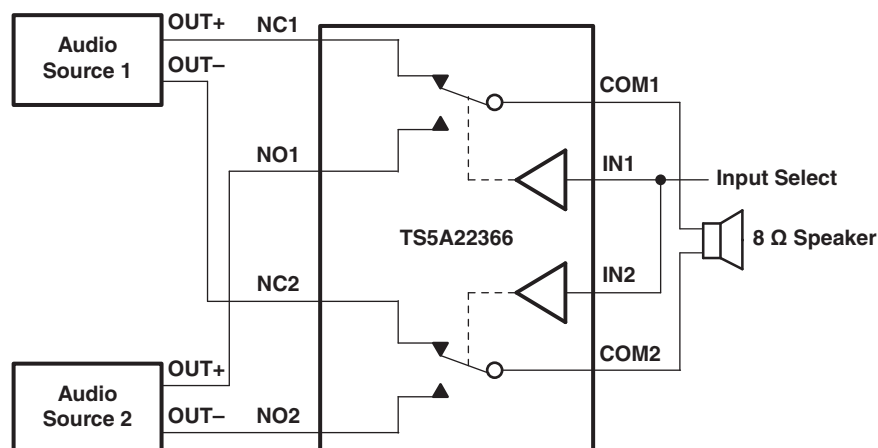


Figure 1. TS5A22366 Application Block Diagram

Negative Signaling Capacity

The TS5A22366 dual SPDT switch features negative signal capability that allows signals below ground to pass through without distortion. These analog switches operate from a single +2.3-V to +5.5-V supply. The input/output signal swing of the device is dependant of the supply voltage V_+ : the devices pass signals as high as V_+ and as low as $V_+ - 5.5$ V, including signals below ground with minimal distortion.

Table 3 shows the input/output signal swing the user can get with different supply voltages.

Table 3. Input/Output Signal Swing

SUPPLY VOLTAGE, V_+	MINIMUM (V_{NC}, V_{NO}, V_{COM}) = $V_+ - 5.5$	MAXIMUM (V_{NC}, V_{NO}, V_{COM}) = V_+
5.5 V	0 V	5.5 V
4.2 V	-1.3 V	4.2 V
3.3 V	-2.2 V	3.3 V
3 V	-2.5 V	3 V
2.5 V	-3 V	2.5 V

ABSOLUTE MINIMUM AND MAXIMUM RATINGS^{(1) (2)}

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V ₊	Supply voltage range ⁽³⁾		−0.5	6	V
V _{NC} V _{NO} V _{COM}	Analog voltage range ^{(3) (4) (5)}		V ₊ − 6	V ₊ + 0.5	V
I _K	Analog port diode current ⁽⁶⁾	V ₊ < V _{NC} , V _{NO} , V _{COM} < 0	−50	50	V
I _{NC} I _{NO} I _{COM}	ON-state switch current	V _{NC} , V _{NO} , V _{COM} = 0 to V ₊	−150	150	mA
	ON-state peak switch current ⁽⁷⁾		−300	300	
V _I	Digital input voltage range		−0.5	6.5	V
I _{IK}	Digital input clamp current ^{(3) (4)}	V _{IO} < V _I < 0	−50		mA
I _{GND} I ₊	Continuous current through V ₊ or GND		−100	100	mA
T _{stg}	Storage temperature range		−65	150	°C

- (1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (5) This value is limited to 5.5 V maximum.
- (6) Requires clamp diodes on analog port to V_+ .
- (7) Pulse at 1-ms duration <10% duty cycle

THERMAL IMPEDANCE RATINGS

			UNIT
θ_{JA}	Package thermal impedance ⁽¹⁾	YFC package	106.2 °C/W

- (1) The package thermal impedance is calculated in accordance with JESD 51-7.

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY⁽¹⁾
 $V_+ = 2.25\text{ V to }2.7\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch								
Analog signal range	V_{COM}, V_{NO}, V_{NC}				$V_+ - 5.5$		V_+	Ω
ON-state resistance	r_{on}	V_{NC} or $V_{NO} = V_+, 1.5\text{ V}$, $V_+ - 5.5\text{ V}$ $I_{COM} = -100\text{ mA}$, Switch ON, See Figure 15	25°C Full	2.25 V		1	1.8 2	Ω
ON-state resistance match between channels	Δr_{on}	V_{NC} or $V_{NO} = 1.5\text{ V}$, $I_{COM} = -100\text{ mA}$, Switch ON, See Figure 15	25°C Full	2.25 V		0.05	1 1	Ω
ON-state resistance flatness	$r_{on(flat)}$	V_{NC} or $V_{NO} = V_+, 1.5\text{ V}$, $V_+ - 5.5\text{ V}$ $I_{COM} = -100\text{ mA}$, Switch ON, See Figure 16	25°C Full	2.25 V		0.53	1.5 1.6	Ω
NC, NO OFF leakage current	$I_{NC(OFF)}, I_{NO(OFF)}$	$V_{NC} = 2.25, V_+ - 5.5\text{ V}$ $V_{COM} = V_+ - 5.5\text{ V}$, 2.25, $V_{NO} = \text{Open}$, or $V_{NO} = 2.25, V_+ - 5.5\text{ V}$ $V_{COM} = V_+ - 5.5\text{ V}$, 2.25, $V_{NC} = \text{Open}$, Switch OFF, See Figure 16	25°C Full	2.7 V	-50		50 375	nA
COM ON leakage current	$I_{COM(ON)}$	V_{NC} and $V_{NO} = \text{Open}$, $V_{COM} = V_+, V_+ - 5.5\text{ V}$, See Figure 17	25°C Full	2.7 V	-50		50 375	nA
Digital Control Inputs (IN, EN)⁽²⁾								
Input logic high	V_{IH}		Full		1.05		5.5	V
Input logic low	V_{IL}		Full				0.65	V
Input leakage current	I_{IH}, I_{IL}	$V_{IN} = 1.8\text{ V or GND}$	25°C Full	2.7 V	-700		700 700	nA

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY⁽¹⁾ (continued)
 $V_+ = 2.25\text{ V to }2.7\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T _A	V ₊	MIN		TYP	MAX	UNIT
Dynamic										
Turn-on time	t _{ON}	V _{COM} = V ₊ , R _L = 300 Ω,	C _L = 35 pF, See Figure 19	25°C	2.5 V	193		297	350	ns
				Full	2.25 V to 2.7 V					
Turn-off time	t _{OFF}	V _{COM} = V ₊ , R _L = 300 Ω,	C _L = 35 pF, See Figure 19	25°C	2.5 V			266	320	ns
				Full	2.25 V to 2.7 V					
Break-before-make time	t _{BBM}	V _{NC} = V _{NO} = V ₊ /2 R _L = 300 Ω,	C _L = 35 pF, See Figure 20	25°C	2.5 V	1	15.6			ns
Charge injection	Q _C	V _{GEN} = 0, R _{GEN} = 0,	C _L = 1 nF, See Figure 24	25°C	2.5 V	91				pC
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V _{NC} or V _{NO} = V ₊ or GND, Switch OFF,	See Figure 18	25°C	2.5 V	51				pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V _{NC} or V _{NO} = V ₊ or GND, Switch OFF,	See Figure 18	25°C	2.5 V	181				pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 18	25°C	2.5 V	181				pF
Digital input capacitance	C _I	V _I = V ₊ or GND	See Figure 18	25°C	2.5 V	3				pF
Bandwidth	BW	R _L = 50 Ω,	Switch ON, See Figure 20	25°C	2.5 V	32				MHz
OFF isolation	O _{ISO}	R _L = 50 Ω, Switch OFF, See Figure 22	f = 100 kHz,	25°C	2.5 V	-70				dB
			f = 1 MHz,			-50				
			f = 5 MHz,			-35				
Crosstalk	X _{TALK}	R _L = 50 Ω, Switch ON, See Figure 23	f = 100 kHz,	25°C	2.5 V	-70				dB
			f = 1 MHz,			-50				
			f = 5 MHz,			-35				
Total harmonic distortion	THD	R _L = 600 Ω, C _L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 25	25°C	2.5 V	0.02				%
Supply										
Positive supply current	I ₊	V _I = 1.8 V or GND,		Full	2.7 V	6		12	μA	

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY⁽¹⁾
 $V_+ = 3\text{ V to }3.6\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V _{COM} , V _{NO} , V _{NC}					V ₊ − 5.5		V ₊	Ω
ON-state resistance	r _{on}	V _{NC} or V _{NO} ≤ V ₊ , 1.5 V, V ₊ − 5.5 V, I _{COM} = −100 mA, Switch ON, See Figure 15	25°C	3 V	0.8		1.3	Ω	
			Full		1.53				
ON-state resistance match between channels	Δr _{on}	V _{NC} or V _{NO} = 1.5 V, I _{COM} = −100 mA, Switch ON, See Figure 15	25°C	3 V	0.08		0.17	Ω	
			Full		0.3				
ON-state resistance flatness	r _{on(flat)}	V _{NC} or V _{NO} ≤ V ₊ , 1.5 V, V ₊ − 5.5 V, I _{COM} = −100 mA, Switch ON, See Figure 16	25°C	3 V	0.3		0.65	Ω	
			Full		0.75				
NC, NO OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}	V _{NC} = 3, V ₊ − 5.5 V V _{COM} = V ₊ − 5.5 V, 3, V _{NO} = Open, or V _{NO} = 3, V ₊ − 5.5 V V _{COM} = V ₊ − 5.5 V, 3, V _{NC} = Open, Switch OFF, See Figure 16	25°C	3.6 V	−50		50	nA	
			Full		−375		375		
COM ON leakage current	I _{COM(ON)}	V _{NC} and V _{NO} = Open, V _{COM} = V ₊ , V ₊ − 5.5 V, Switch ON, See Figure 17	25°C	3.6 V	−50		50	nA	
			Full		−375		375		
Digital Control Inputs (IN, EN) ⁽²⁾									
Input logic high	V _{IH}			Full		1.05		5.5	V
Input logic low	V _{IL}			Full				0.65	V
Input leakage current	I _{IH} , I _{IL}	V _{IN} = 1.8 V or GND		25°C	3.6 V	−920		920	nA
				Full		−920		920	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY⁽¹⁾ (continued)
 $V_+ = 3\text{ V to }3.6\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T _A	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t _{ON}	V _{COM} = V ₊ , R _L = 300 Ω,	C _L = 35 pF, See Figure 19	25°C	3.3 V	199	313	ns	
				Full	3 V to 3.6 V		370		
Turn-off time	t _{OFF}	V _{COM} = V ₊ , R _L = 300 Ω,	C _L = 35 pF, See Figure 19	25°C	3.3 V	182	289.9	ns	
				Full	3 V to 3.6 V		350		
Break-before-make time	t _{BBM}	V _{NC} = V _{NO} = V ₊ /2 R _L = 300 Ω,	C _L = 35 pF, See Figure 20	25°C	3.3 V	1	7.1	ns	
Charge injection	Q _C	V _{GEN} = 0, R _{GEN} = 0,	C _L = 1 nF, See Figure 24	25°C	3.3 V		120	pC	
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V _{NC} or V _{NO} = V ₊ or V ₊ – 5.5 V, Switch OFF,	See Figure 18	25°C	3.3 V		50	pF	
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V _{NC} or V _{NO} = V ₊ or GND, Switch OFF,	See Figure 18	25°C	3.3 V		180	pF	
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 18	25°C	3.3 V		180	pF	
Digital input capacitance	C _I	V _I = V ₊ or GND	See Figure 18	25°C	3.3 V		3	pF	
Bandwidth	BW	R _L = 50 Ω,	Switch ON, See Figure 20	25°C	3.3 V		32	MHz	
OFF isolation	O _{ISO}	R _L = 50 Ω, Switch OFF, See Figure 22	f = 100 kHz,	25°C	3.3 V		–70	dB	
			f = 1 MHz,				–50		
			f = 5 MHz,				–35		
Crosstalk	X _{TALK}	R _L = 50 Ω, Switch ON, See Figure 23	f = 100 kHz,	25°C	3.3 V		–70	dB	
			f = 1 MHz,				–50		
			f = 5 MHz,				–35		
Total harmonic distortion	THD	R _L = 600 Ω, C _L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 25	25°C	3.3 V		0.01	%	
Supply									
Positive supply current	I ₊	V _I = 1.8 V or GND		Full	3.6 V		6	13	μA

ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY⁽¹⁾
 $V_+ = 4.5 \text{ V to } 5.5 \text{ V}$, $T_A = -40^\circ\text{C to } 85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch								
Analog signal range	$V_{\text{COM}}, V_{\text{NO}}, V_{\text{NC}}$				$V_+ - 5.5$		V_+	Ω
ON-state resistance	r_{on}	V_{NC} or $V_{\text{NO}} = V_+$, 1.5V, $V_+ - 5.5\text{V}$ $I_{\text{COM}} = -100 \text{ mA}$, Switch ON, See Figure 15	25°C Full	4.5 V	0.7	1		Ω
ON-state resistance match between channels	Δr_{on}	V_{NC} or $V_{\text{NO}} = 1.5 \text{ V}$, $I_{\text{COM}} = -100 \text{ mA}$, Switch ON, See Figure 15	25°C Full	4.5 V	0.1	0.2	0.3	Ω
ON-state resistance flatness	$r_{\text{on(flat)}}$	V_{NC} or $V_{\text{NO}} = V_+$, 1.5V, $V_+ - 5.5\text{V}$ $I_{\text{COM}} = -100 \text{ mA}$, Switch ON, See Figure 16	25°C Full	4.5 V	0.135	0.37	0.51	Ω
NC, NO OFF leakage current	$I_{\text{NC(OFF)}}, I_{\text{NO(OFF)}}$	$V_{\text{NC}} = 4.5, V_+ - 5.5 \text{ V}$ $V_{\text{COM}} = V_+ - 5.5 \text{ V}$, 4.5, $V_{\text{NO}} = \text{Open}$, or $V_{\text{NO}} = 4.5, V_+ - 5.5 \text{ V}$ $V_{\text{COM}} = V_+ - 5.5 \text{ V}$, 4.5, $V_{\text{NC}} = \text{Open}$, Switch OFF, See Figure 16	25°C Full	5.5 V	-50		50	nA
COM ON leakage current	$I_{\text{COM(ON)}}$	V_{NC} and $V_{\text{NO}} = \text{Open}$, $V_{\text{COM}} = V_+, V_+ - 5.5 \text{ V}$, Switch ON, See Figure 17	25°C Full	5.5 V	-50		50	nA
Digital Control Inputs (IN, EN)⁽²⁾								
Input logic high	V_{IH}		Full		1.05		5.5	V
Input logic low	V_{IL}		Full				0.65	V
Input leakage current	$I_{\text{IH}}, I_{\text{IL}}$	$V_{\text{IN}} = 1.8 \text{ V or } 0$	25°C Full	5.5 V	-1.5		1.5	μA

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY⁽¹⁾ (continued)
 $V_+ = 4.5 \text{ V to } 5.5 \text{ V}$, $T_A = -40^\circ\text{C to } 85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T _A	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t _{ON}	V _{COM} = V ₊ , R _L = 300 Ω,	C _L = 35 pF, See Figure 19	25°C	5 V		230	374	ns
				Full	4.5 V to 5.5 V			470	
Turn-off time	t _{OFF}	V _{COM} = V ₊ , R _L = 300 Ω,	C _L = 35 pF, See Figure 19	25°C	5 V		206	325	ns
				Full	4.5 V to 5.5 V			380	
Break-before-make time	t _{BBM}	V _{NC} = V _{NO} = V ₊ /2, R _L = 300 Ω,	C _L = 35 pF, See Figure 20	25°C	3.3 V	1	3		ns
Charge injection	Q _C	V _{GEN} = 0, R _{GEN} = 0,	C _L = 1 nF, See Figure 24	25°C	5 V		168		pC
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V _{NC} or V _{NO} = V ₊ or V ₊ – 5.5 V, Switch OFF,	See Figure 18	25°C	5 V		48		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V _{NC} or V _{NO} = V ₊ or V ₊ – 5.5 V, Switch ON,	See Figure 18	25°C	5 V		176		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 18	25°C	5 V		176		pF
Digital input capacitance	C _I	V _I = V ₊ or GND	See Figure 18	25°C	5 V		3		pF
Bandwidth	BW	R _L = 50 Ω,	Switch ON, See Figure 20	25°C	5 V		32		MHz
OFF isolation	O _{ISO}	R _L = 50 Ω, Switch OFF, See Figure 22	f = 100 kHz	25°C	5 V		–70		dB
			f = 1 MHz				–50		
			f = 5 MHz				–35		
Crosstalk	X _{TALK}	R _L = 50 Ω, Switch ON, See Figure 23	f = 100 kHz	25°C	5 V		–70		dB
			f = 1 MHz				–50		
			f = 5 MHz				–35		
Total harmonic distortion	THD	R _L = 600 Ω, C _L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 25	25°C	5 V		0.01		%
Supply									
Positive supply current	I ₊	V _I = 1.8 V or GND		Full	5.5 V		7	14	μA

TYPICAL PERFORMANCE

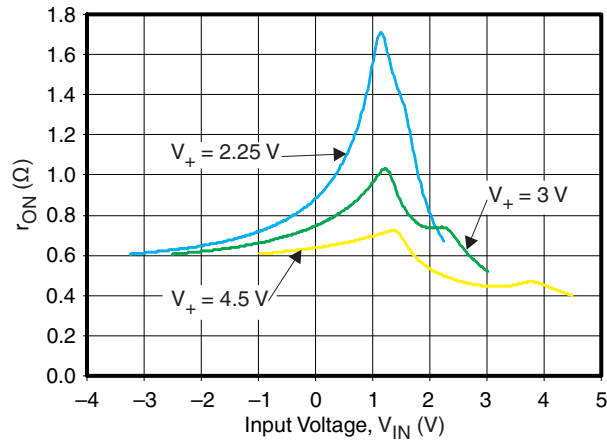


Figure 2. r_{on} vs V_{IN}

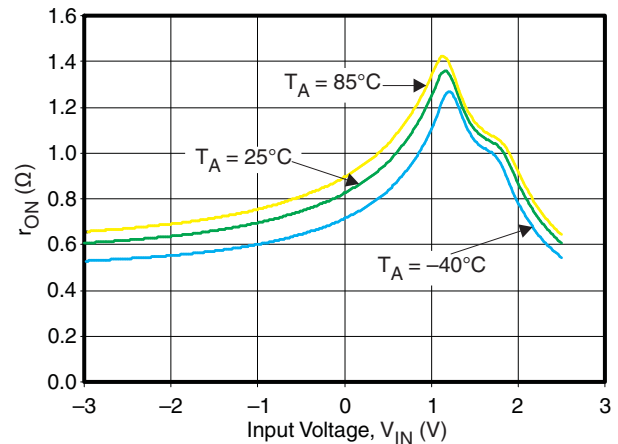


Figure 3. r_{on} vs V_{IN} ($V_+ = 2.5$ V)

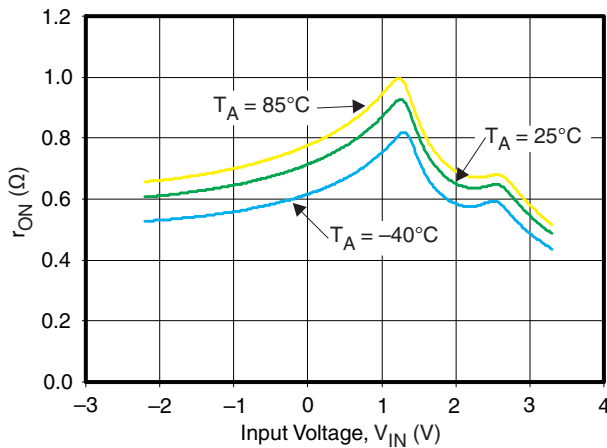


Figure 4. r_{on} vs V_{IN} ($V_+ = 3.3$ V)

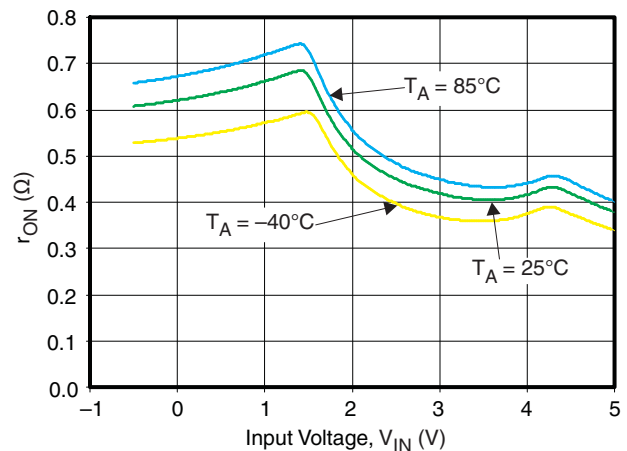


Figure 5. r_{on} vs V_{IN} ($V_+ = 5$ V)

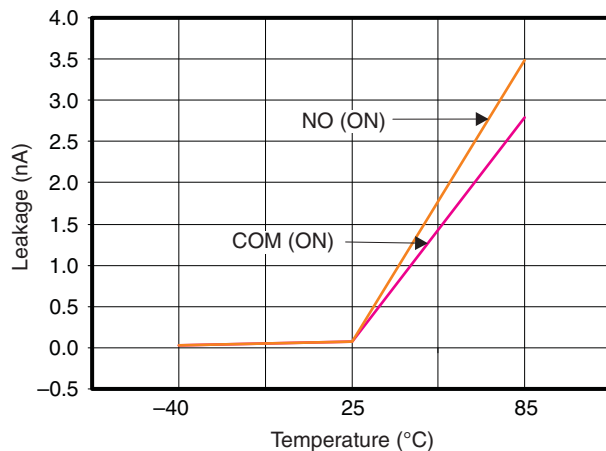


Figure 6. Leakage Current vs Temperature

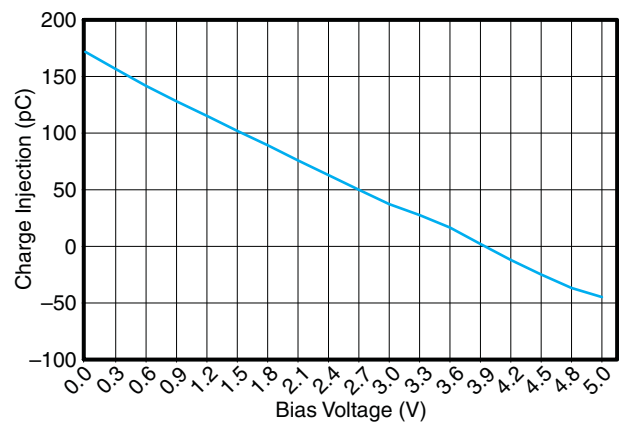
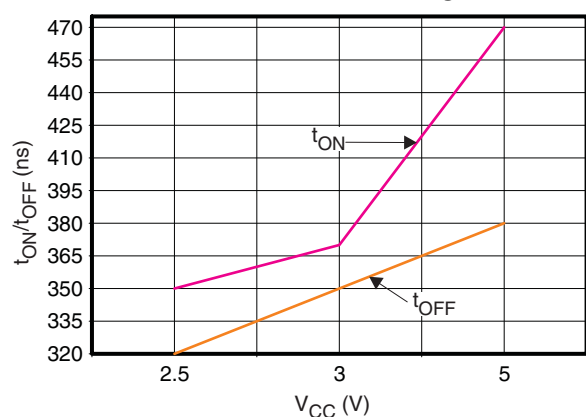
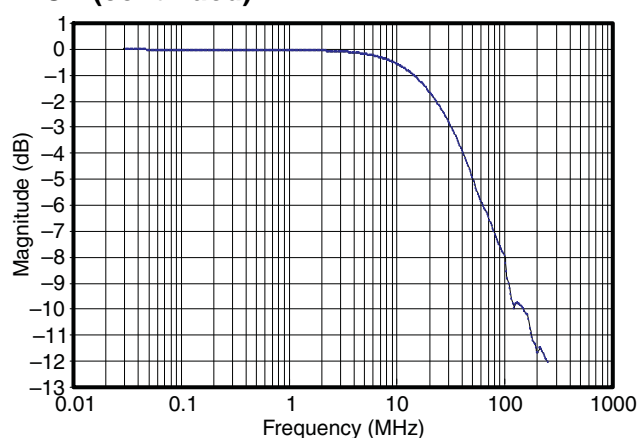
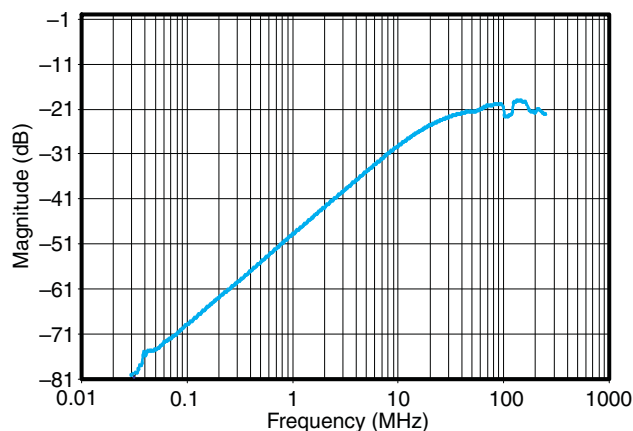
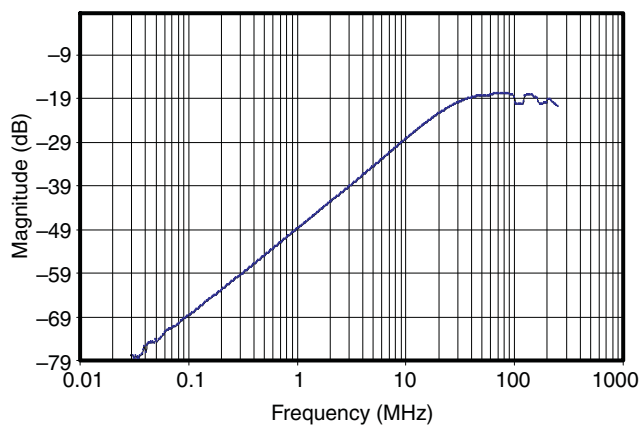
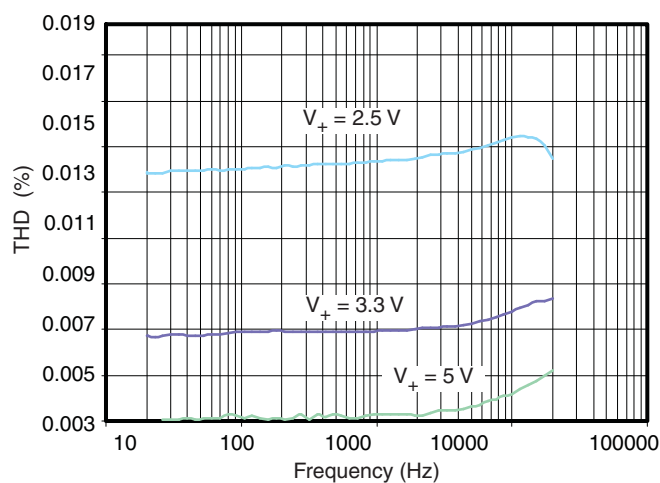
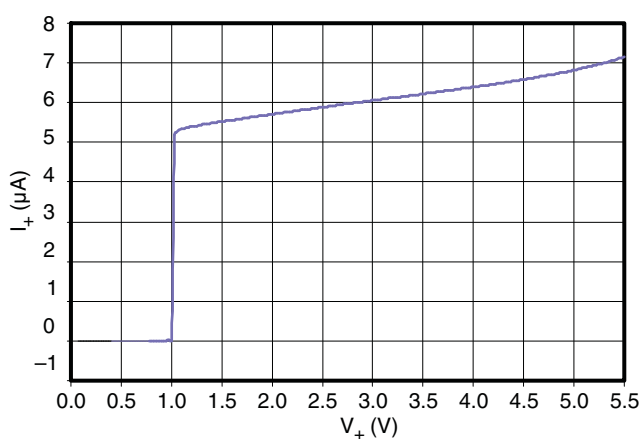


Figure 7. Charge Injection (Q_C) vs V_{COM} ($V_+ = 5$ V)

TYPICAL PERFORMANCE (continued)**Figure 8. t_{ON} and t_{OFF} vs Supply Voltage****Figure 9. Bandwidth (V₊ = 2.5 V)****Figure 10. OFF Isolation vs Frequency****Figure 11. Crosstalk (V₊ = 3.3 V)****Figure 12. Total Harmonic Distortion vs Frequency****Figure 13. Power-Supply Current vs V₊**

TYPICAL PERFORMANCE (continued)

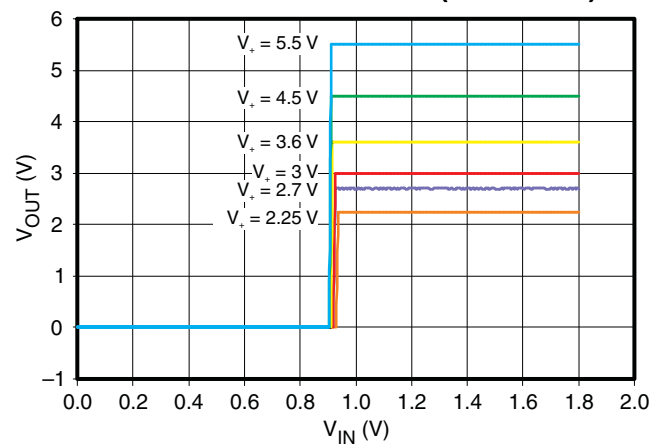


Figure 14. Control Input Thresholds

PARAMETER MEASUREMENT INFORMATION

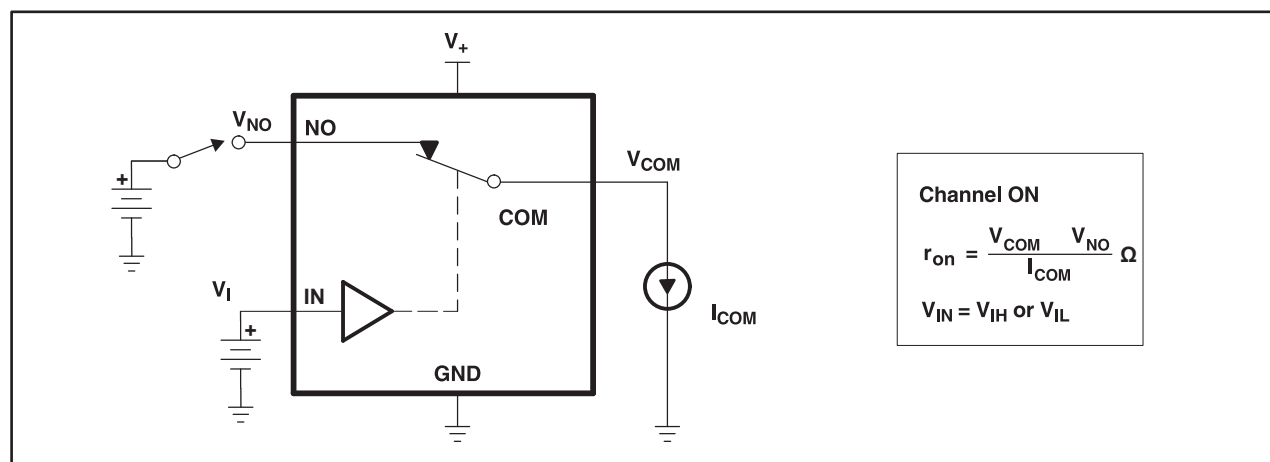


Figure 15. ON-state Resistance (r_{ON})

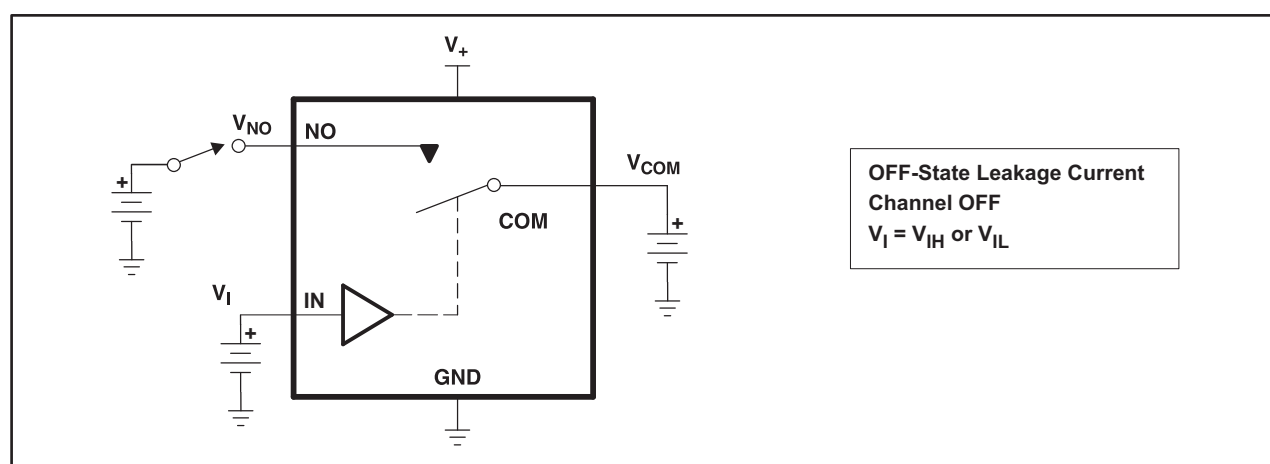


Figure 16. OFF-State Leakage Current
($I_{COM(OFF)}$, $I_{NC(OFF)}$, $I_{COM(PWROFF)}$, $I_{NC(PWROFF)}$)

PARAMETER MEASUREMENT INFORMATION (continued)

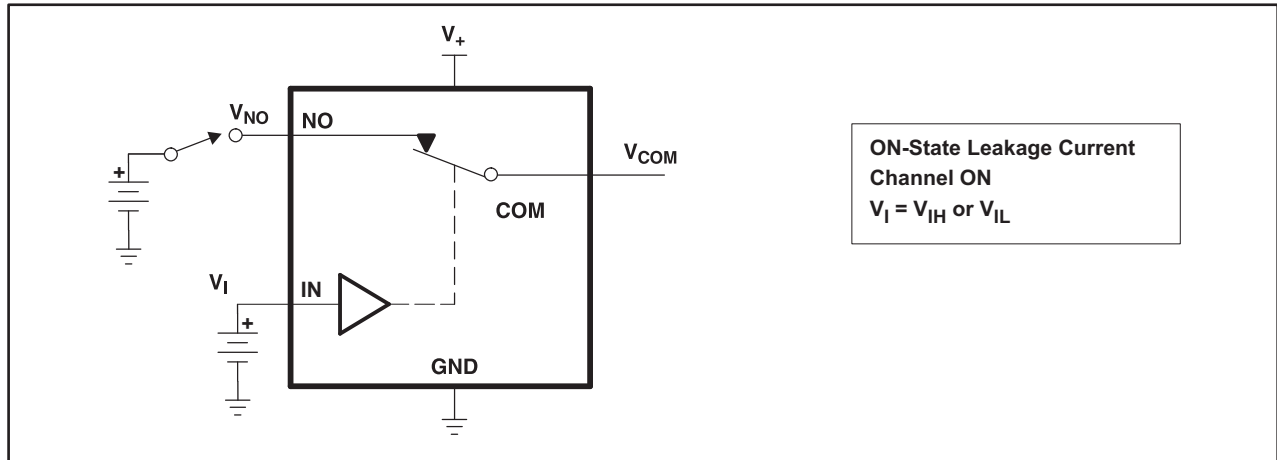


Figure 17. ON-State Leakage Current
($I_{COM(ON)}$, $I_{NC(ON)}$)

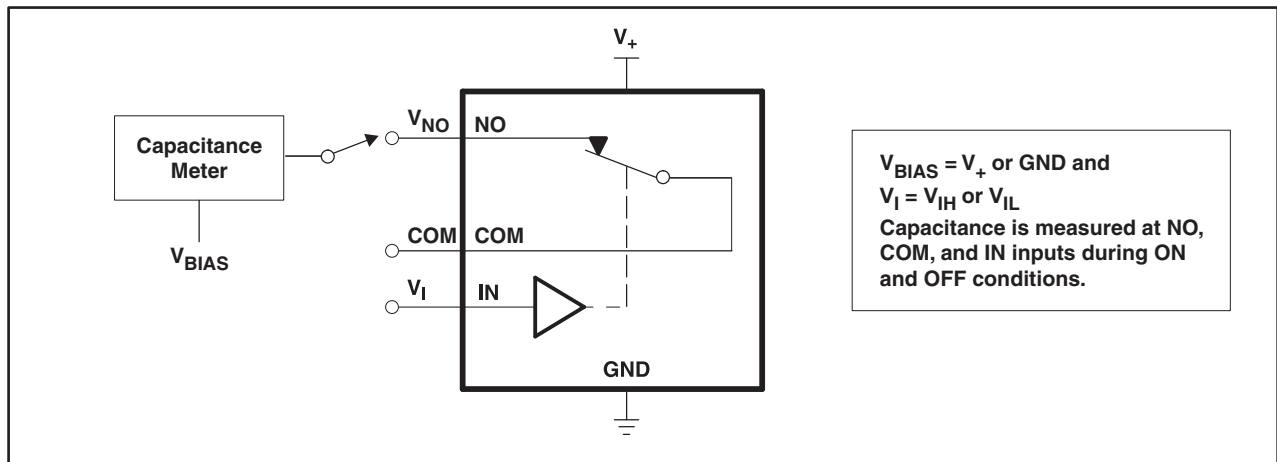
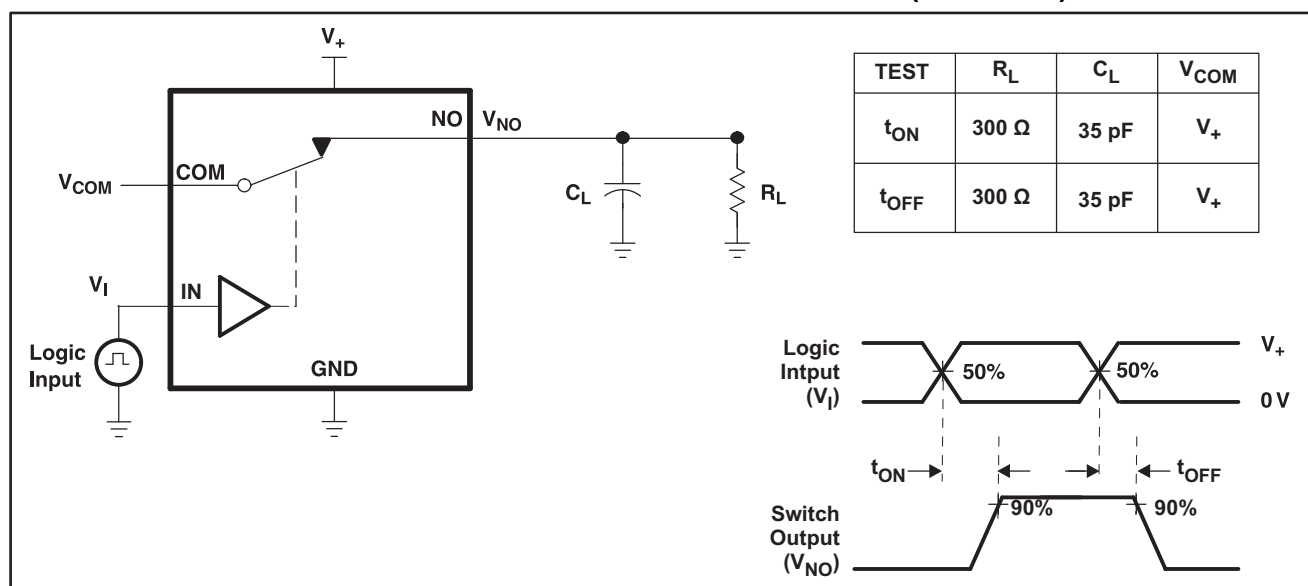
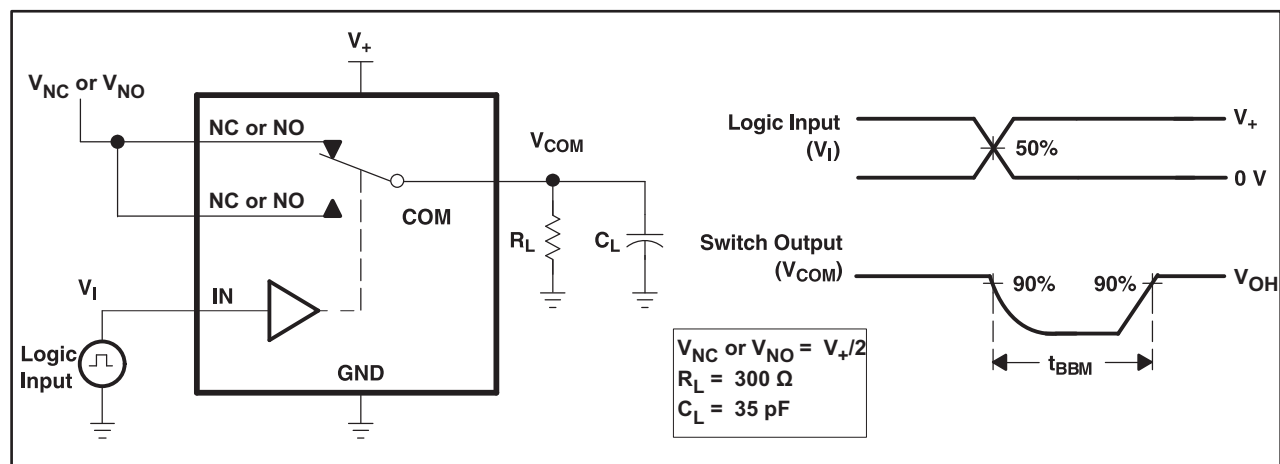


Figure 18. Capacitance
(C_I , $C_{COM(OFF)}$, $C_{COM(ON)}$, $C_{NC(OFF)}$, $C_{NC(ON)}$)

- A. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r < 5 \text{ ns}$, $t_f < 5 \text{ ns}$.
- B. C_L includes probe and jig capacitance.

PARAMETER MEASUREMENT INFORMATION (continued)**Figure 19. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})**

- A. C_L includes probe and jig capacitance.
- B. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r < 5$ ns, $t_f < 5$ ns.

**Figure 20. Break-Before-Make Time (t_{BBM})**

PARAMETER MEASUREMENT INFORMATION (continued)

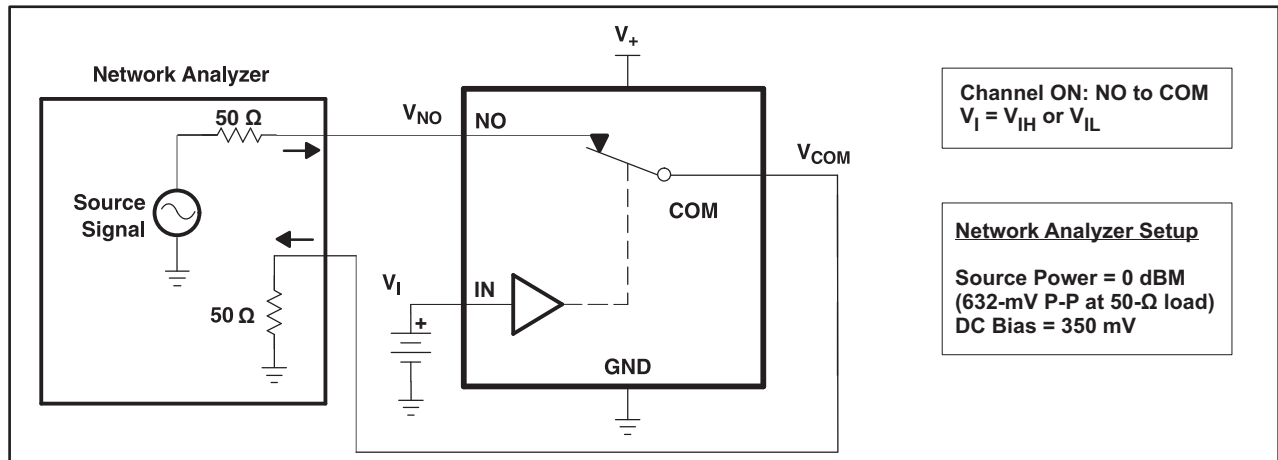


Figure 21. Bandwidth (BW)

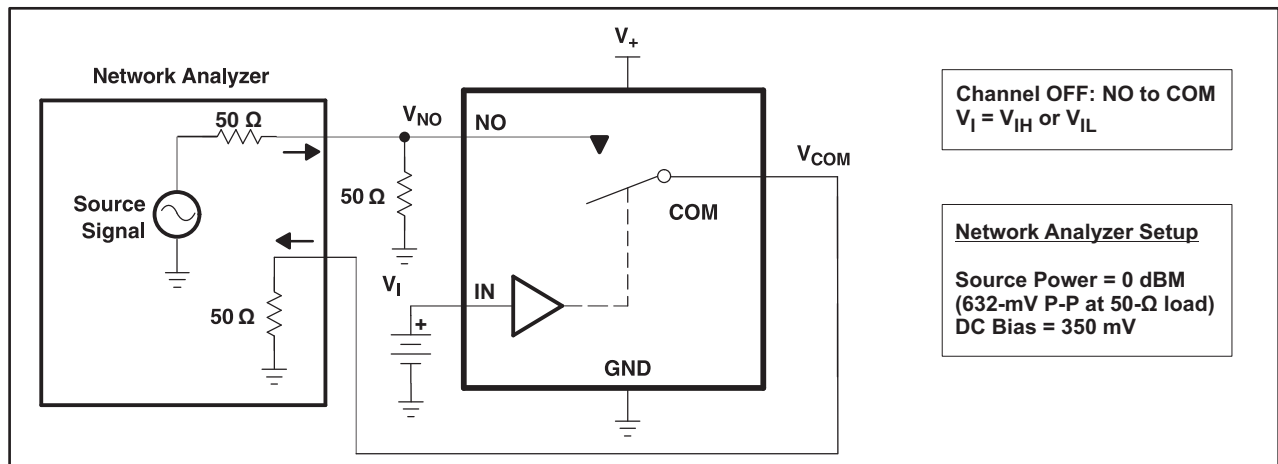


Figure 22. OFF Isolation (O_{ISO})

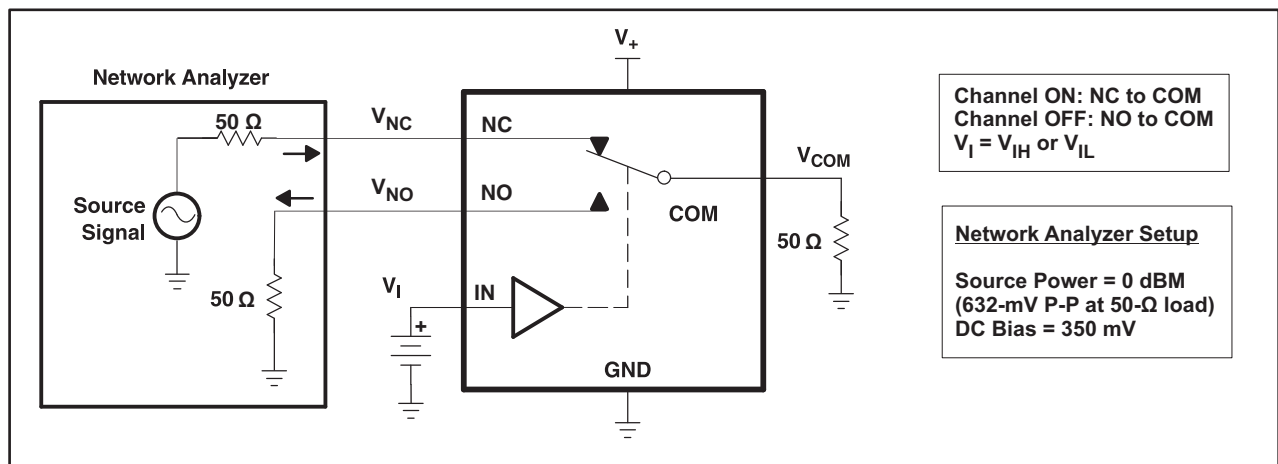
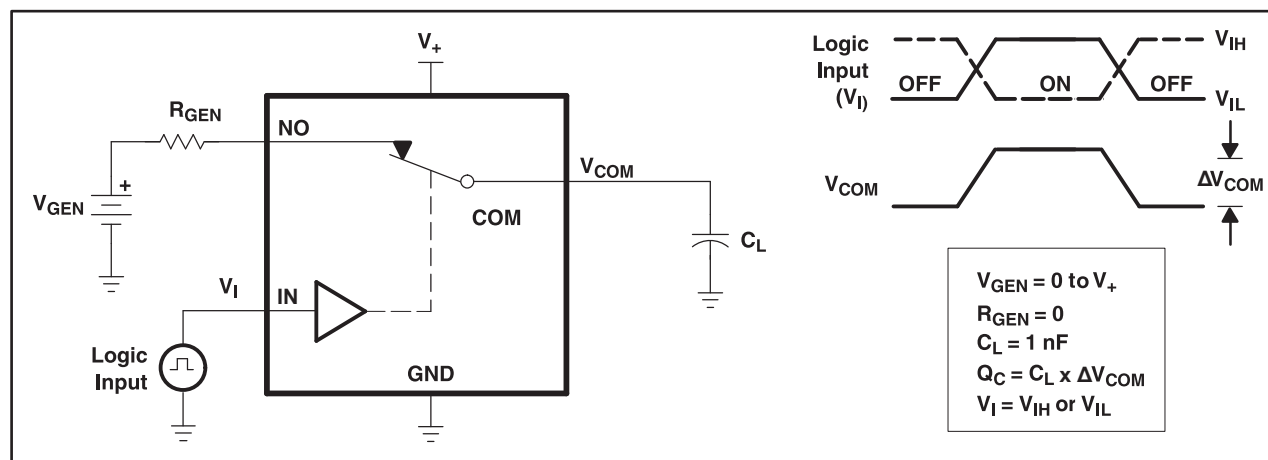
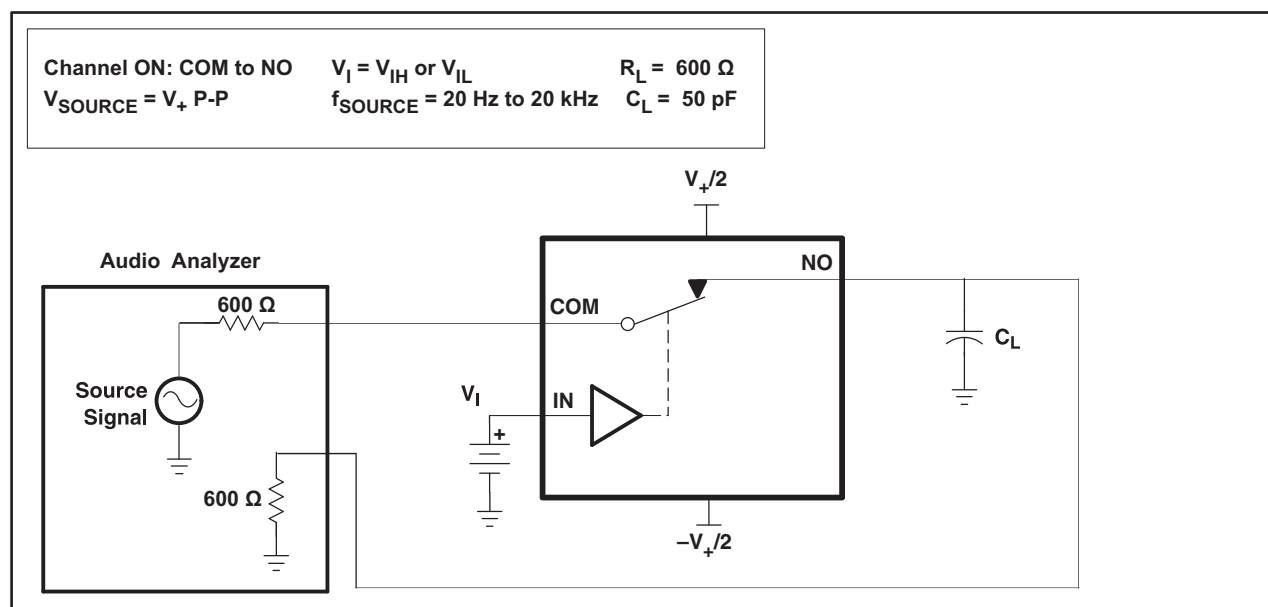


Figure 23. Crosstalk (X_{TALK})

- All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_r < 5 ns, t_f < 5 ns.
- C_L includes probe and jig capacitance.

PARAMETER MEASUREMENT INFORMATION (continued)**Figure 24. Charge Injection (Q_C)**

A. C_L includes probe and jig capacitance.

**Figure 25. Total Harmonic Distortion (THD)**

REVISION HISTORY

Changes from Revision A (August 2009) to Revision B	Page
<ul style="list-style-type: none"> Removed QFN reference from product description. Changed Analog signal range MIN value from $V_+ - 0.5$ to $V_+ - 5.5$ 	1 7

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TS5A22366YFCR	ACTIVE	DSBGA	YFC	12	3000	Green (RoHS & no Sb/Br)	Call TI SNAGCU	Level-1-260C-UNLIM	-40 to 85	(3A2 ~ 3AN)	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A22366YFCR	DSBGA	YFC	12	3000	178.0	9.2	1.29	1.69	0.73	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS

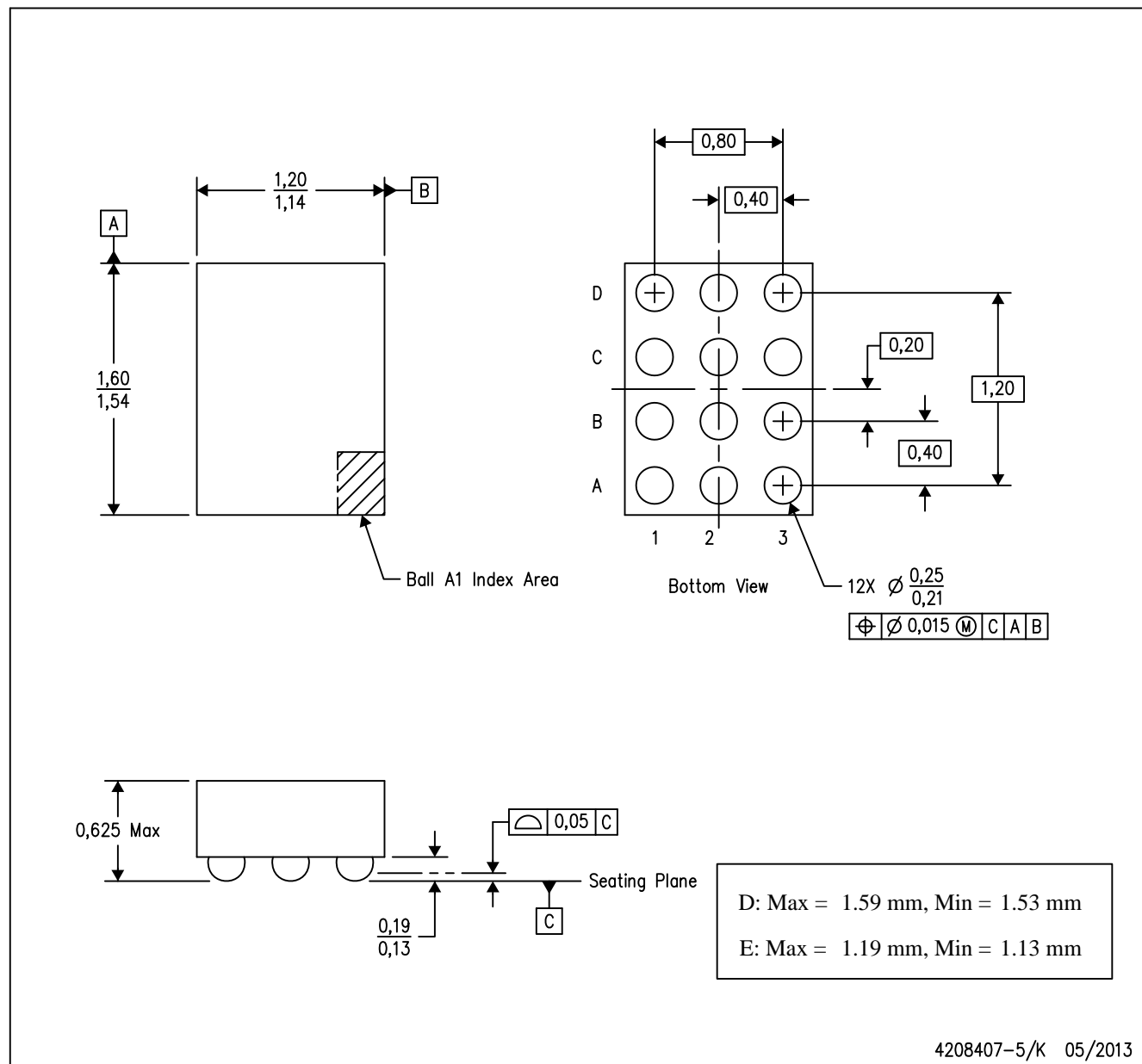


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A22366YFCR	DSBGA	YFC	12	3000	220.0	220.0	35.0

YFC (R-XBGA-N12)

DIE-SIZE BALL GRID ARRAY



- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. NanoFree™ package configuration.

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